

IN THE CLAIMS:

1-2. (Canceled)

3. (Original) A semiconductor device, comprising a gate electrode formed over a gate insulating film and a hard mask formed over the gate electrode.

4. (Currently Amended) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film;
a hard mask formed over the gate electrode, and
a conductive film which is ~~to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting the wire with the gate electrode and~~ is in contact with the gate electrode,

wherein the conductive film is to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting a wire with the gate electrode.

5-8. (Canceled)

9. (Original) A semiconductor device, according to claim 3, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

10. (Original) A semiconductor device, according to claim 3, wherein the hard mask is selected from the group consisting of silicon oxide.

11. (Original) A semiconductor device, according to claim 4, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

12. (Original) A semiconductor device, according to claim 4, wherein the hard mask is selected from the group consisting of silicon oxide.

13. (Original) A semiconductor device, according to claim 4, wherein the conductive film is selected from the group consisting of tantalum nitride and tungsten.

14. (New) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film; and,
an island shaped hard mask formed over the gate electrode,
wherein side walls of the island shaped hard mask have an angle of inclination of 0°
or more, and of 90° or less.
15. (New) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film; and,
an island shaped hard mask formed over the gate electrode,
wherein side walls of the island shaped hard mask forms arc shapes.
16. (New) A semiconductor device, according to claim 14, wherein the angle is
inclination of 35° or more, and 50° or less.
17. (New) A semiconductor device, according to claim 14, wherein the gate electrode
is selected from the group consisting of tantalum nitride and tungsten.
18. (New) A semiconductor device, according to claim 14, wherein the island shaped
hard mask is selected from the group consisting of silicon oxide.
19. (New) A semiconductor device, according to claim 15, wherein the gate electrode
is selected from the group consisting of tantalum nitride and tungsten.
20. (New) A semiconductor device, according to claim 15, wherein the island shaped
hard mask is selected from the group consisting of silicon oxide.
21. (New) A semiconductor device, comprising:
a gate electrode formed over a gate insulating film;
an island shaped hard mask formed over the gate electrode; and
a conductive film which is in contact with the gate electrode,

wherein the conductive film is to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting a wire with the gate electrode, and

wherein side walls of the island shaped hard mask have an angle of inclination of 0° or more, and of 90° or less.

22. (New) A semiconductor device, comprising:

a gate electrode formed over a gate insulating film;

an island shaped hard mask formed over the gate electrode; and

a conductive film which is in contact with the gate electrode,

wherein the conductive film is to serve as a wire for sending a signal to the gate electrode or as a connection layer for connecting a wire with the gate electrode, and

wherein side walls of the island shaped hard mask forms arc shapes.

23. (New) A semiconductor device, according to claim 21, wherein the angle is inclination of 35° or more, and 50° or less.

24. (New) A semiconductor device, according to claim 21, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

25. (New) A semiconductor device, according to claim 21, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.

26. (New) A semiconductor device, according to claim 22, wherein the gate electrode is selected from the group consisting of tantalum nitride and tungsten.

27. (New) A semiconductor device, according to claim 22, wherein the island shaped hard mask is selected from the group consisting of silicon oxide.